IN THE SPECIFICATION:

Please amend paragraph [0020] as follows.

[0020] The processes are performed until the length of the grain is about 10 micrometers [[(□)]] (μm), and the silicon layer including the grains may be used as an active layer of a thin film transistor, which has a channel of about 6 micrometers [[(□)]] (μm) in width.

Please amend paragraph [0022] as follows.

[0022] As shown in FIG. 3, a plurality of blocking layers 22 spaced apart from each other is formed on a base substrate 20. Spaces between the blocking layers 22 are defined as slits 24. The base substrate 20 may be formed of quartz, and the blocking layers 22 may be formed of chromium (Cr), which reflects a laser beam. The blocking layers 22 may have a width of about 4 micrometers [[(□)]] (μm), and the slits 24 may have a width of about 2 micrometers [[(□)]] (μm).

Please amend paragraph [0026] as follows.

[0026] Although not shown in FIG. 4, distance C between the two peaks of the first laser shot is closely connected to the width of the blocking layer 22 of the mask 20 of FIG. 3 (*i.e.*, a space between the slits 24 of FIG. 3). Since the peaks of each laser shot must have the distance C therebetween to prevent them from overlapping each other, there is a limitation in reducing the width of the blocking layer 22 under 4 micrometers [[(□)]] (μm) according to the structure of the mask of the related art.

Please amend paragraph [0027] as follows.

[0027] More particularly, in the SLS crystallizing process using the mask of the related art, if the peaks of a laser shot overlap each other, the silicon layer is melted non-uniformly because an overlapping portion between the peaks is large, and thus the grains do not grow completely. In addition, since a nucleation region is formed in the overlapping portion, characteristics of crystallization get worse. Therefore, the width of the blocking layer, that is, the space between the slits must be more than at least 4 micrometers [[(□)]] (μm) so that the peaks of each laser shot do not overlap each other, thereby providing a reliable process. However, there is a disadvantage in that the efficiency of the process is lowered due to an increase in the laser shots.

Please amend paragraph [0057] as follows.

[0057] In the mask of the present invention, the third width W3 of the slit 116 may be within the range of about 1 to 3 micrometers [[(□)]] (μm), and the first width W1 of the phase shift layer 112 may be also within the range of about 1 to 3 micrometers [[(□)]] (μm). It may be beneficial that the third width W3 and the first width W1 are about 2 micrometers [[(□)]] (μm). Accordingly, in the present invention, the resolution of the mask for crystallizing can be improved due to a destructive interference of the beam profile by using the phase shift layer without changing the optical compensating apparatus for controlling the laser beam. Therefore, productivity in the SLS crystallizing method can be increased due to the mask having an improved resolution.

Please amend paragraph [0062] as follows.

[0062] Accordingly, although the mask may have the resolution of about 2 micrometers [[(□)]] (µm), for example, the profiles of the laser beam do not overlap each other, and thus the growth of grains can be stable and reproducible.